## AMT1224 0.1 – 6GHz Low Noise Amplifier Chip

#### **Key Features:**

Frequency range: 0.1 – 6GHz

• Typical gain: 21dB

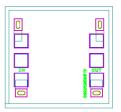
Input standing wave : 1.5Output standing wave : 1.1

• Noise figure: 2.0dB

P-1 : 17dBm @ +5V/65mA

• Chip dimensions: 0.75mm x 0.8mm x 0.1mm

• Applications: wireless communication, transceiver module, radio telecommunication etc.



### **Description:**

AMT1224 chip is a Gallium Arsenide (GaAs) high performance Low Noise Amplifier, it covers 0.1 – 6GHz frequency range. It uses +5V single voltage operation, noise figure is 2.0dB, and 21dB typical gain. This chip is designed with ground through metal vias on the back technology.

### **Absolute Maximum Ratings (Ta = 25°C)**

| Symbol | Parameter             | Value        | Remark             |
|--------|-----------------------|--------------|--------------------|
| Vd     | Drain Voltage         | +7V          |                    |
| Pin    | Input Signal Power    | 17dBm        |                    |
| Tch    | Operating Temperature | 150°C        |                    |
| Tm     | Sintering Temperature | 310°C        | 30s, N₂ protection |
| Tstg   | Storage Temperature   | -65 ~ +150°C |                    |

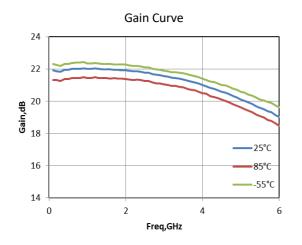
[1] Operation outside any of the Absolute Maximum Ratings may cause permanent device damage.

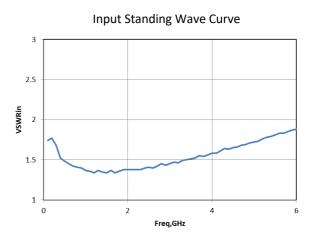
#### **Electrical Characteristics (Ta = 25°C)**

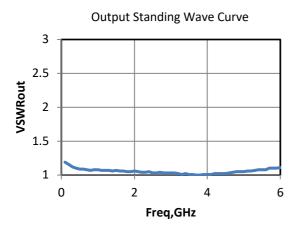
| Symbol   | Parameter                 | Test Conditions | Value |         | Unit |     |  |
|----------|---------------------------|-----------------|-------|---------|------|-----|--|
|          |                           |                 | Min   | Typical | Max  |     |  |
| G        | Gain                      |                 | -     | 21      | -    | dB  |  |
| NF       | Noise Figure              |                 | -     | 2       | 2.2  | dB  |  |
| Id       | Static Current            | Vd = +5V        | -     | 65      | -    | mA  |  |
| VSWR_in  | Input Standing Wave       | F : 0.1 ~ 6GHz  | -     | 1.5     | 1.8  | -   |  |
| VSWR_out | Output Standing Wave      |                 | -     | 1.1     | 1.2  | -   |  |
| P-1      | Output Power at 1dB point |                 | 15.8  | 17      | -    | dBm |  |

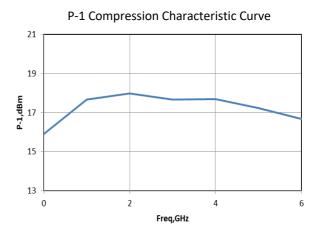
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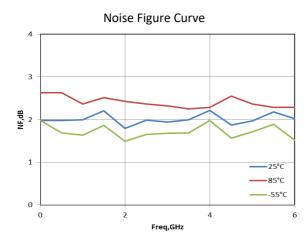
## **Typical Performance**





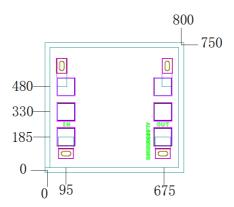




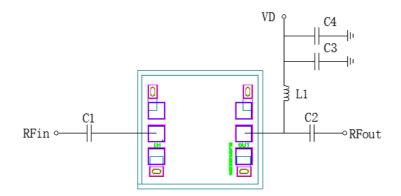


# AMT1224 0.1 – 6GHz Low Noise Amplifier Chip

## Chip Dimensions (Unit: µm)



## **Chip Layout Diagram**



| Frequency   | 100MHz | 1GHz       | 2GHz |
|-------------|--------|------------|------|
| L1(nH)      | 270    | 47         | 22   |
| C1, C2 (pF) | 200    | 20         | 10   |
| C3/C4 (μF)  |        | 0.001/0.01 |      |

### **Pad Definition**

| Symbol | Function Description   | Demensions  |
|--------|--|-------------|
| RFin   | RF signal input port, connecting to external $50\Omega$ system, need to add DC blocking  | 100μm*100μm |
|        | capacitor.   |             |
| RFout  | RF signal output port, connecting to external $50\Omega$ system, need to add DC blocking | 100μm*100μm |
|        | capacitor.   |             |
| VD     | +5V single operation voltage   |             |

Please see Appendix A for details.